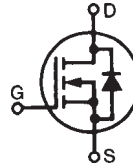


PolarHV™ HiPerFET IXFR 36N60P

Power MOSFET

(Electrically Isolated Back Surface)

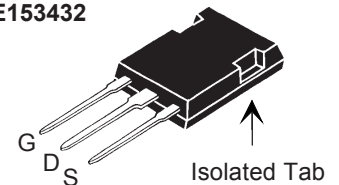
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



V_{DSS}	=	600	V
I_{D25}	=	20	A
$R_{DS(on)}$	≤	200	mΩ
t_{rr}	≤	200	ns

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	600	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	$T_C = 25^\circ\text{C}$	20	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	80	A
I_{AR}	$T_C = 25^\circ\text{C}$	36	A
E_{AR}	$T_C = 25^\circ\text{C}$	50	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\ \Omega$	20	V/ns
P_D	$T_C = 25^\circ\text{C}$	208	$^\circ\text{C}$
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS, 1 minute	2500	V~
F_C	Mounting force	20..120/4.6..27	N/lb
Weight		5	g

ISOPLUS247 (IXFR)
E153432



G = Gate D = Drain
S = Source

Features

- † Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- † International standard package
- † Fast recovery diode
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
- easy to drive and to protect

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 250\ \mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30\text{ V}$, $V_{DS} = 0\text{ V}$			±100 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$ $T_J = 125^\circ\text{C}$			25 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = I_T$ (note 1) Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			200 mΩ

Advantages

- † Easy to mount
- † Space savings
- † High power density

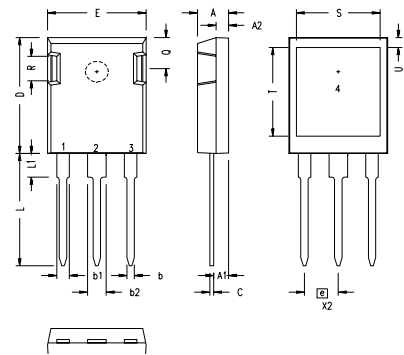
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{ V}; I_D = I_T$, pulse test	25	40	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		5800	pF
C_{oss}			570	pF
C_{rss}			30	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_T$ $R_G = 2\ \Omega$ (External)		30	ns
t_r			25	ns
$t_{d(off)}$			80	ns
t_f			22	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_T$		102	nC
Q_{gs}			34	nC
Q_{gd}			36	nC
R_{thJC}			0.6	$^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Note 1: Test current $I_T = 18\text{ A}$

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			36 A
I_{SM}	Repetitive			80 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}, V_{GS} = 0\text{ V}$			200 ns
Q_{RM}			0.8	μC
I_{RM}			6.0	A

ISOPLUS247 (IXFR) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585
one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405B2 6,759,692
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

Fig. 1. Output Characteristics @ 25°C

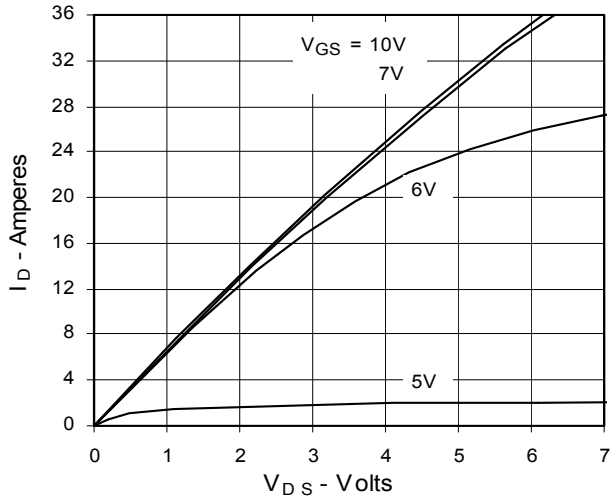


Fig. 2. Extended Output Characteristics @ 25°C

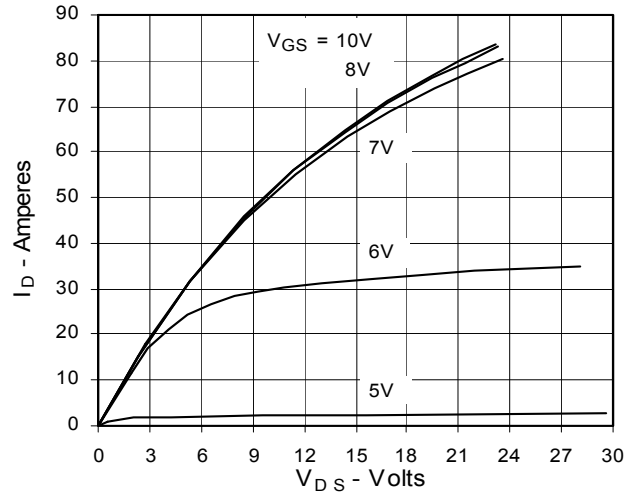


Fig. 3. Output Characteristics @ 125°C

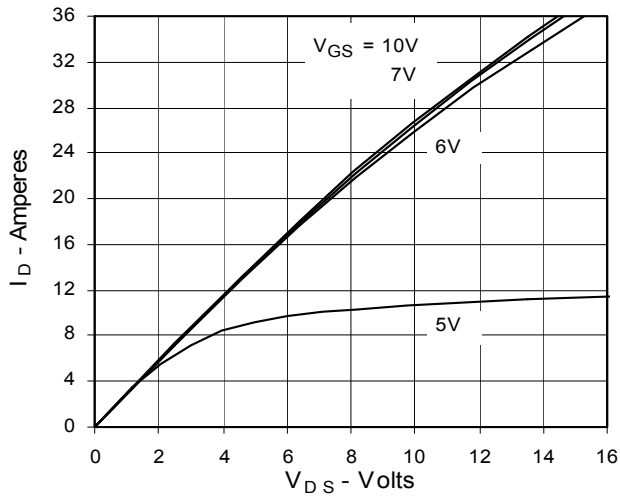


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 18A$ Value vs. Junction Temperature

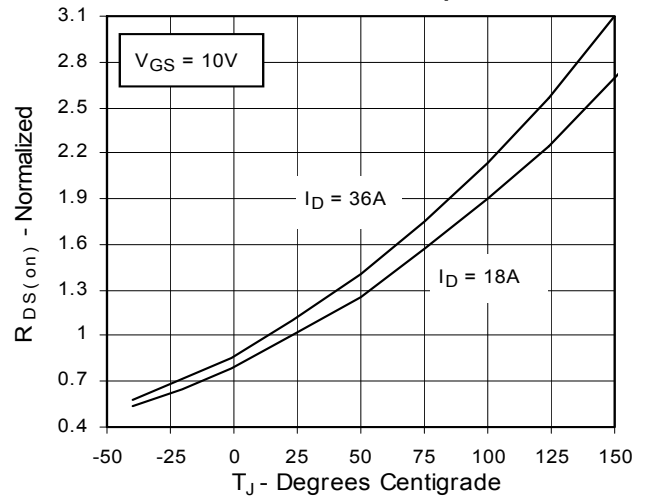


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 18A$ Value vs. I_D

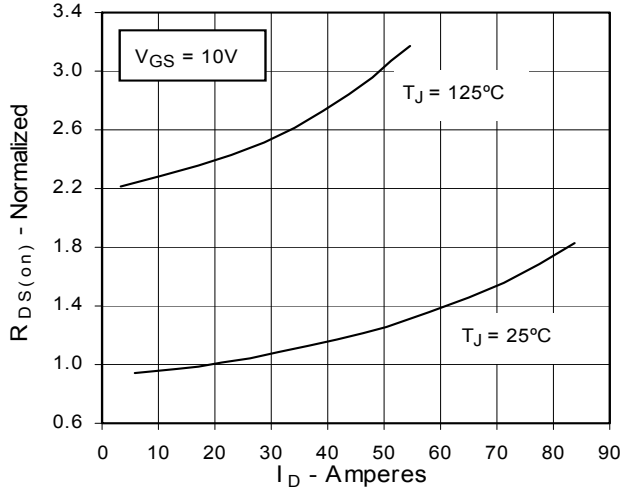


Fig. 6. Drain Current vs. Case Temperature

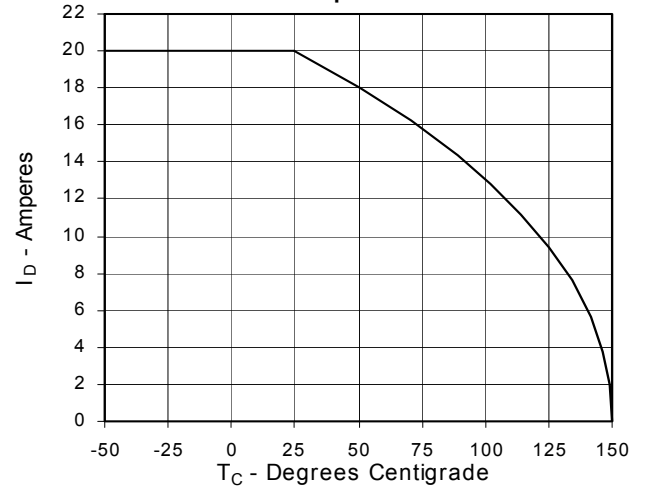


Fig. 7. Input Admittance

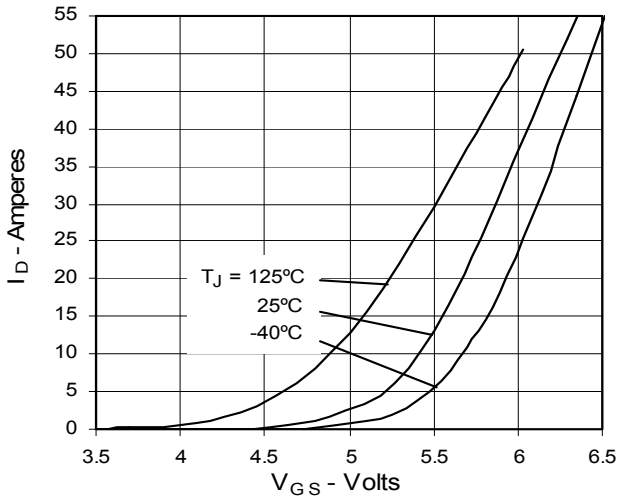


Fig. 8. Transconductance

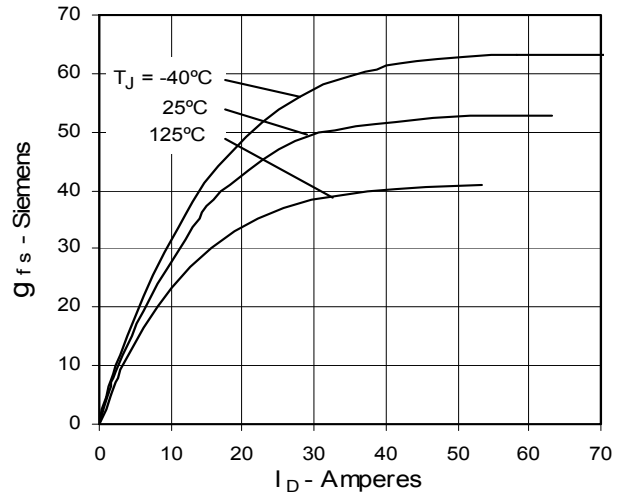


Fig. 9. Source Current vs. Source-To-Drain Voltage

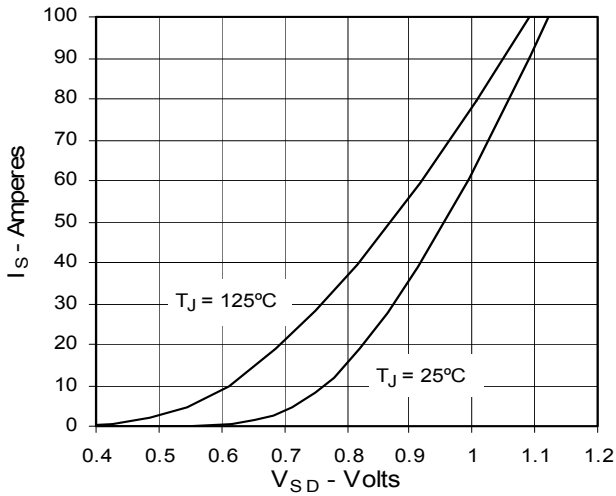


Fig. 10. Gate Charge

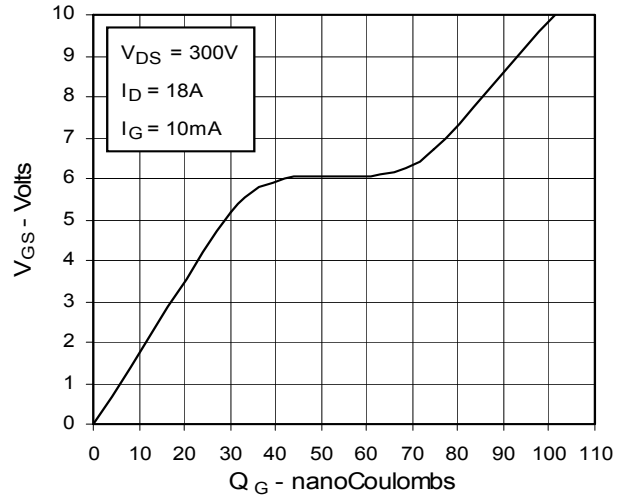


Fig. 11. Capacitance

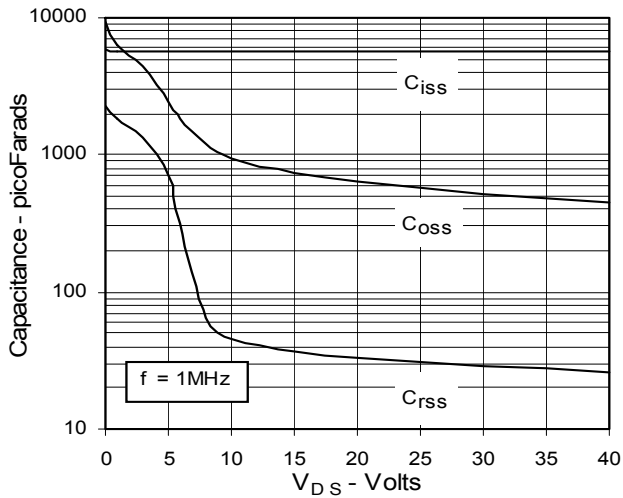


Fig. 12. Maximum Transient Thermal Resistance

